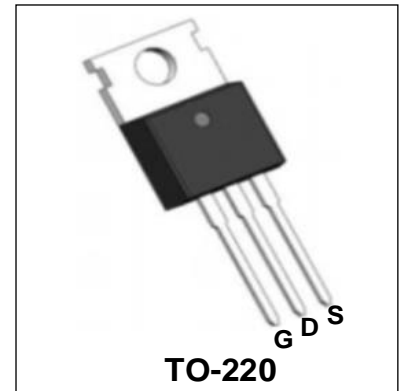


80V N-Channel Enhancement Mode Power MOSFET

Description

WMK037N08HG2 uses Wayon's 2nd generation power trench MOSFET technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance. This device is well suited for high efficiency fast switching applications.

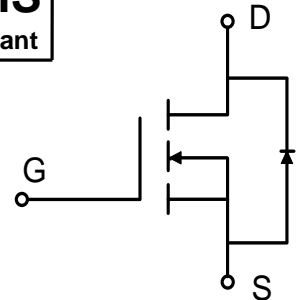


Features

- $V_{DS} = 80V$, $I_D = 190A$ (Silicon Limited)
 $R_{DS(on)} < 3.9m\Omega @ V_{GS} = 10V$
- High Speed Power Switching
- Low $R_{DS(ON)}$
- Low Gate Charge
- 100% EAS Guaranteed

Applications

- Synchronous Rectification in SMPS
- Hard Switching and High Speed Circuit
- Power Tools
- UPS
- Motor Control



Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹ (Silicon Limited)	$T_C=25^\circ C$	I_D	190	A
	$T_C=100^\circ C$		128	
Continuous Drain Current ¹ (Package Limited)	$T_C=25^\circ C$		180	
Pulsed Drain Current ²		I_{DM}	501	A
Single Pulse Avalanche Energy ³		EAS	304	mJ
Avalanche Current		I_{AS}	39	A
Total Power Dissipation ⁴	$T_C=25^\circ C$	P_D	267	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ¹	$R_{\theta JA}$	59	$^\circ C/W$
Thermal Resistance from Junction-to-Case ¹	$R_{\theta JC}$	0.56	$^\circ C/W$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80	-	-	V	
Gate-body Leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	$T_J = 25^\circ\text{C}$	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$	-	-	1	μA
	$T_J = 100^\circ\text{C}$			-	-	100	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V	
Drain-Source on-Resistance ²	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$	-	3.4	3.9	m Ω	
Forward Transconductance ²	g_{fs}	$V_{DS} = 5V, I_D = 20A$	-	68	-	S	
Dynamic Characteristics							
Input Capacitance	C_{iss}	$V_{DS} = 40V, V_{GS} = 0V,$ $f = 1\text{MHz}$	-	3648	-	μF	
Output Capacitance	C_{oss}		-	1280	-		
Reverse Transfer Capacitance	C_{rss}		-	76	-		
Switching Characteristics							
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V,$ $f = 1\text{MHz}$	-	1.2	-	Ω	
Total Gate Charge	Q_g	$V_{DS} = 40V, V_{GS} = 10V,$ $I_D = 20A$	-	73	-	nC	
Gate-Source Charge	Q_{gs}		-	18	-		
Gate-Drain Charge	Q_{gd}		-	30	-		
Turn-on Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 40V,$ $R = 10\Omega, I_D = 20A$	-	13.5	-	nS	
Rise Time	t_r		-	17.5	-		
Turn-off Delay Time	$t_{d(off)}$		-	45	-		
Fall Time	t_f		-	26	-		
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ²	V_{SD}	$I_S = 1A, V_{GS} = 0V$	-	-	1.0	V	
Body Diode Reverse Recovery Time	t_{rr}	$V_R = 40V, I_F = 20A,$ $di/dt = 400A/\mu s$	-	45	-	nS	
Body Diode Reverse Recovery Charge	Q_{rr}		-	156	-	nC	

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.4mH, I_{AS} = 39A$
4. The power dissipation is limited by 150°C junction temperature

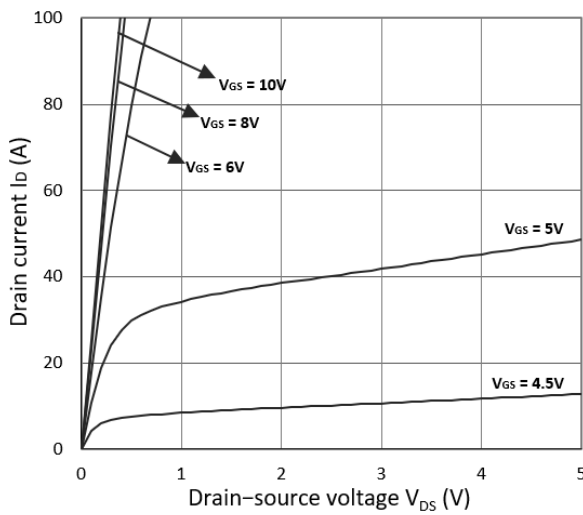


Figure 1. Output Characteristics

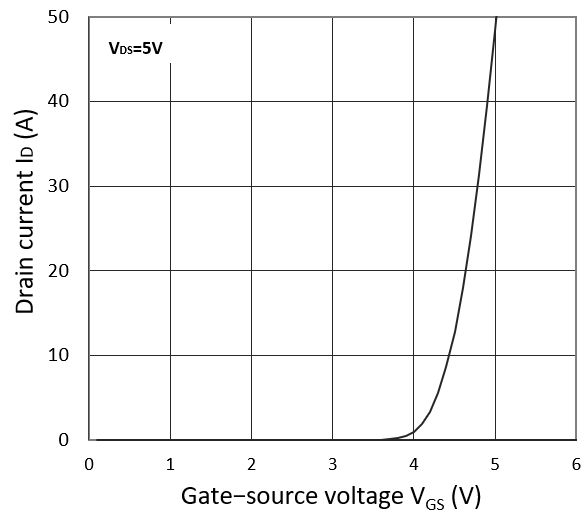


Figure 2. Transfer Characteristics

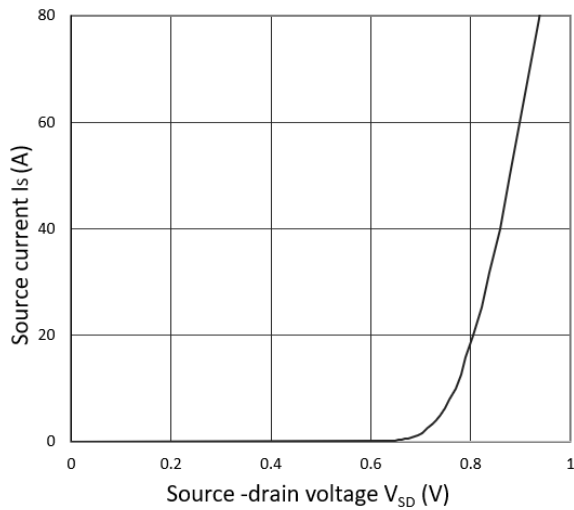


Figure 3. Forward Characteristics of Reverse

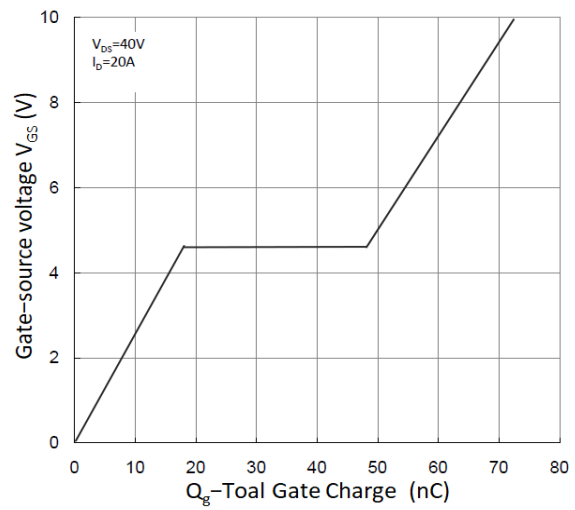


Figure 4. Gate Charge Characteristics

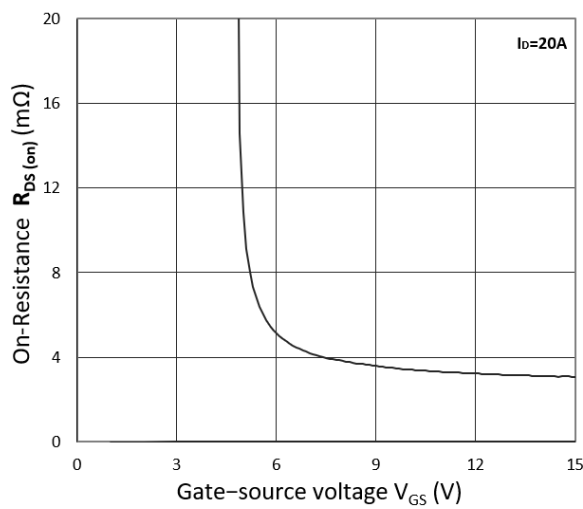


Figure 5. $R_{DS(ON)}$ vs. V_{GS}

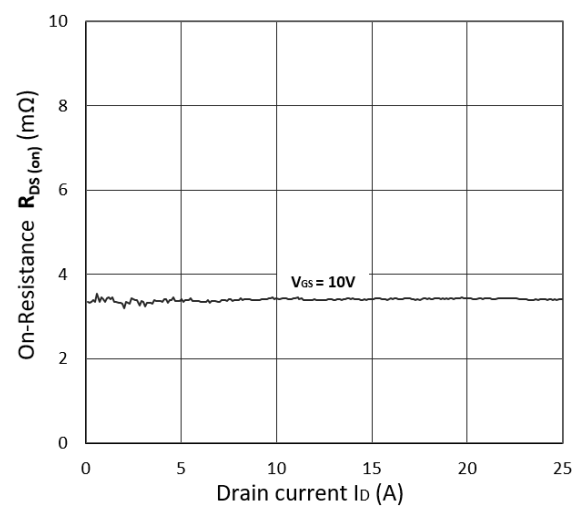


Figure 6. $R_{DS(ON)}$ vs. I_D

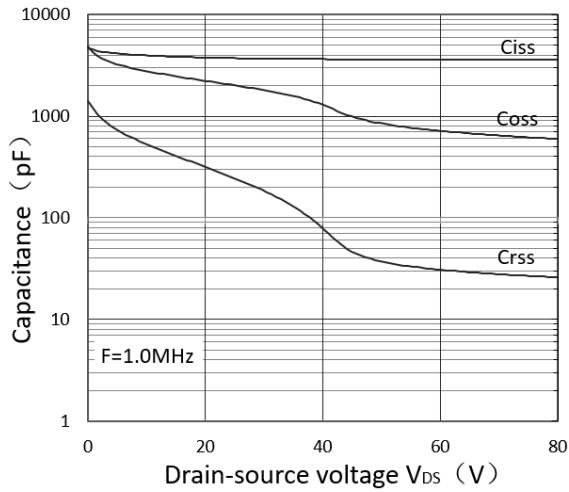


Figure 7. Capacitance Characteristics

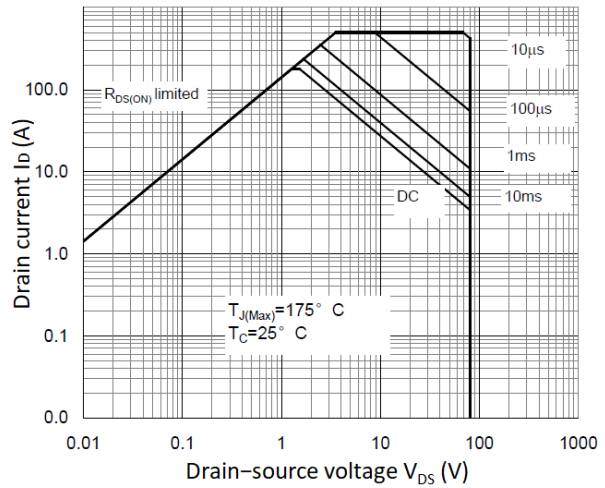


Figure 8. Safe Operating Area

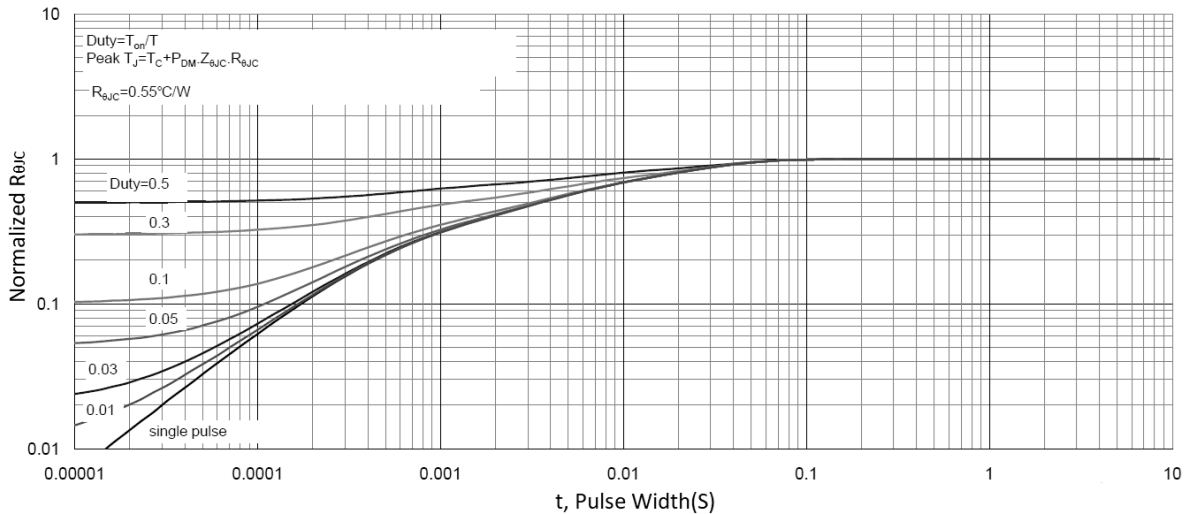


Figure 9. Normalized Maximum Transient Thermal Impedance

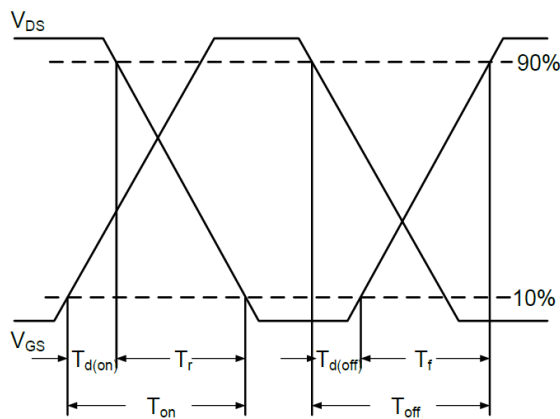


Figure 10. Switching Time Waveform

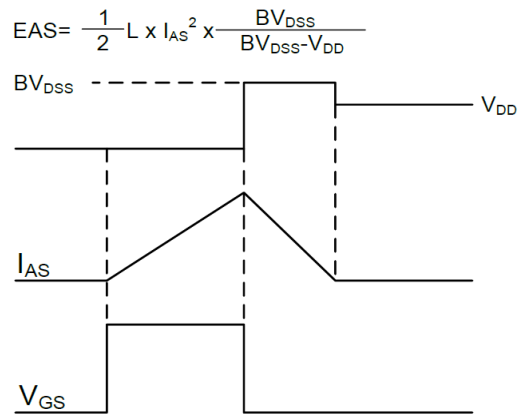
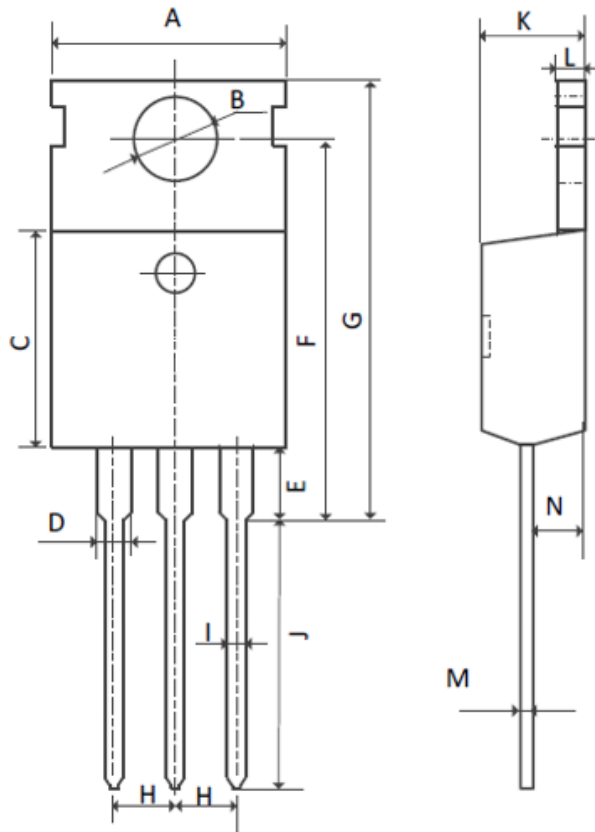


Figure 11. Unclamped Inductive Switching Waveform

Mechanical Dimensions for TO-220



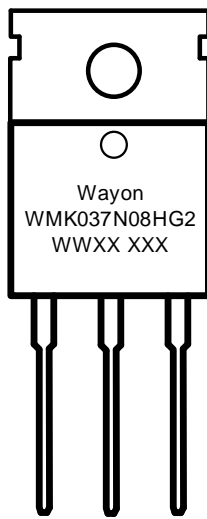
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.40
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

Ordering Information

Part	Package	Marking	Packing method
WMK037N08HG2	TO-220	WMK037N08HG2	Tube

Marking Information



WMK037N08HG2 = Device code
 WWXX XXX = Date code

Contact Information.

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WAYON website: <http://www.way-on.com>

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